Vishay Semiconductors





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SOT-227

FEATURES

- Two fully independent diodes
- Fully insulated package



- High voltage rectifiers optimized for very low COMPLIANT forward voltage drop
- · Industry standard outline
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

These devices are intended for use in main rectification. Single or three phase bridge.

| PRIMARY CHARACTERISTICS | | | | | | | |
|-------------------------------------------------------------|--------------------------------|--|--|--|--|--|--|
| I _{F(AV)} per module | 160 A, T _C = 101 °C | | | | | | |
| V _{FM} typical at 100 A | 1.16 V | | | | | | |
| Туре | Modules - diode, high voltage | | | | | | |
| Package | SOT-227 | | | | | | |
| Circuit configuration Two separate diodes, parallel pin-out | | | | | | | |

| MAJOR RATINGS AND CHARACTERISTICS | | | | | | | | |
|-----------------------------------|-----------------|------------------------|--------------------|--|--|--|--|--|
| SYMBOL | CHARACTERISTICS | CHARACTERISTICS VALUES | | | | | | |
| I _{F(AV)} | 90 °C | 91 | | | | | | |
| I _{F(RMS)} | | 138 | | | | | | |
| | 50 Hz | 940 | — A | | | | | |
| IFSM | 60 Hz | 985 | | | | | | |
| l ² t | 50 Hz | 4420 | — A ² s | | | | | |
| 14 | 60 Hz | 4015 | A2S | | | | | |
| l²√t | | 44 180 | A²√s | | | | | |
| V _{RRM} | | 1200 | V | | | | | |
| TJ | | -55 to +150 | °C | | | | | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | | | | | | |
|-----------------|-----------------|-------------------------------------------------------------------|------------------------------------------------------------------------|---------------------------------------------|--|--|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V _{RRM,} MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V | I _{RRM} TYPICAL AT 150 °C mA | | | | | |
| VS-RA160FA120 | 120 | 1200 | 1300 | 1.0 | | | | | |



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| FORWARD CONDUCTION | | | | | | |
|-------------------------------------------------------------|---------------------|---------------------------------------------------------------------------------|---------------------------|-----------------------------------------------------------------------------|--------|------------------|
| PARAMETER | SYMBOL | | TEST CON | VALUES | UNITS | |
| Maximum average forward current at case temperature per leg | I _{F(AV)} | 180° condu | iction, half sine | wave, 90 °C | 91 | А |
| Maximum RMS forward current per leg | I _{F(RMS)} | DC at 101 ° | °C case temper | ature | 138 | |
| | | t = 10 ms | No voltage | | 940 | |
| Maximum peak, one-cycle forward, | | t = 8.3 ms | reapplied | | 985 | A |
| non-repetitive surge current per leg | I _{FSM} | t = 10 ms | 100 % V _{RRM} | Sinusoidal half wave, initial T _J = T _J maximum | 790 | |
| | | t = 8.3 ms | reapplied | | 825 | |
| | | t = 10 ms | No voltage | | 4420 | A ² s |
| Maximum 12t fax fusing new lag | l ² t | t = 8.3 ms | reapplied | | 4015 | |
| Maximum I ² t for fusing per leg | | t = 10 ms | 100 % V _{RRM} | | 3125 | |
| | | t = 8.3 ms | reapplied | | 2840 | |
| Maximum $I^2 \sqrt{t}$ for fusing per leg | l²√t | t = 0.1 ms t | o 10 ms, no vo | Itage reapplied | 44 180 | A²√s |
| Low level of threshold voltage per leg | V _{F(TO)1} | (16 7 0/ x - | | | 0.80 | V |
| Low level value of forward slope resistance | r _{f1} | (16.7 % x π x $I_{F(AV)}$) < I < π x $I_{F(AV)}$, $T_J = T_J$ maximum | | | 4.32 | mΩ |
| High level of threshold voltage per leg | V _{F(TO)2} | $(I > \pi \times I_{F(AV)}), T_J = T_J maximum$ | | | 0.93 | V |
| High level value of forward slope resistance | r _{f2} | | | | 4.14 | mΩ |
| Maximum famound voltage dwap per lag | N | I _{FM} = 100 A | , T _J = 25 °C | 1.27 | V | |
| Maximum forward voltage drop per leg | V _{FM} | I _{FM} = 100 A | , T _J = 150 °C | | 1.22 | V |

| BLOCKING | | | | |
|--------------------------------------|------------------|------------------------------------------------------------|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum peak reverse leakage current | | T _J = 25 °C | 150 | μA |
| per leg | IRRM | T _J = 150 °C | 1.5 | mA |
| RMS insulation voltage | V _{INS} | $T_J = 25 \text{ °C}$, any terminal to case, t = 1 minute | 2500 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | | | | |
|---------------------------------------|------------|-------------------|---------|------|------------|--------------|--|--|--|
| PARAMETER | | SYMBOL | MIN. | TYP. | MAX. | UNITS | | | |
| Thermal resistance, | per leg | Б | - | - | 0.26 | | | | |
| junction to case | per module | R _{thJC} | - | - | 0.13 | °C/W | | | |
| Thermal resistance, case to heatsink | per module | R _{thCS} | - | 0.1 | - | | | | |
| Weight | | | - | 30 | - | g | | | |
| Mounting torque to terminal | | | - | - | 1.1 (9.7) | Nm (lbf. in) | | | |
| Mounting torque to heatsink | | | - | - | 1.8 (15.9) | Nm (lbf. in) | | | |
| Case style | | | SOT-227 | | | | | | |

| DEVICE | S | INE HALF | WAVE CO | NDUCTIO | N | RECTANGULAR WAVE CONDUCTION | | | | UNITS | |
|---------------|-------|----------|---------|---------|-------|-----------------------------|-------|-------|-------|-------|------|
| DEVICE | 180° | 120° | 90° | 60° | 30° | 180° | 120° | 90° | 60° | 30° | °C/W |
| VS-RA160FA120 | 0.109 | 0.122 | 0.149 | 0.213 | 0.355 | 0.069 | 0.119 | 0.159 | 0.223 | 0.358 | 0/10 |

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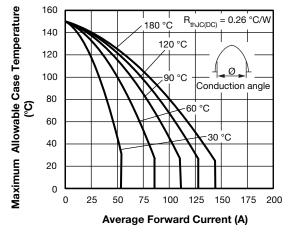


Fig. 1 - Current Ratings Characteristics (A)

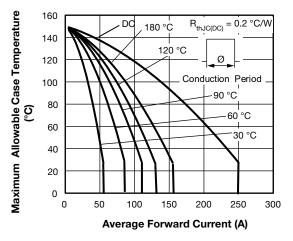


Fig. 2 - Current Ratings Characteristics (A)

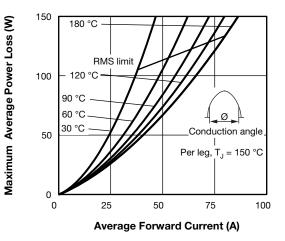


Fig. 3 - Current Ratings Characteristics (A)

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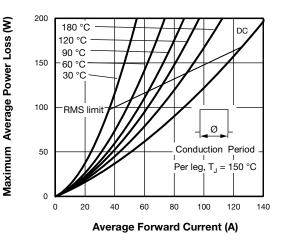


Fig. 4 - Forward Power Loss Characteristics

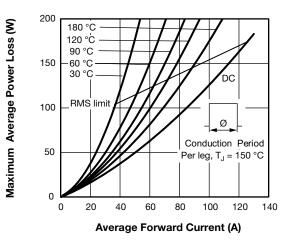


Fig. 5 - Forward Power Loss Characteristics

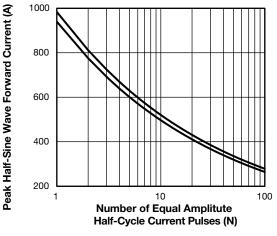


Fig. 6 - Maximum Non-Repetitive Surge Current

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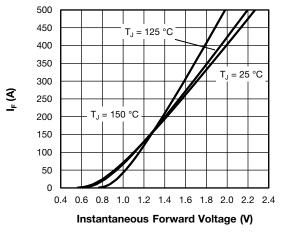


Fig. 7 - Typical Forward Voltage Characteristics

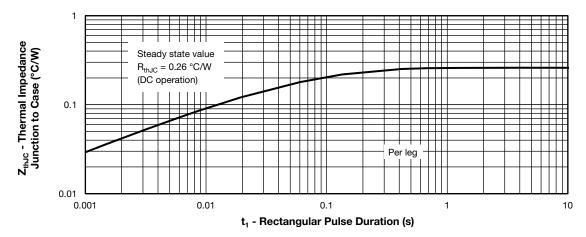


Fig. 8 - Thermal Impedance ZthJC Characteristics

ORDERING INFORMATION TABLE

SHAY

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| Device code | VS- | R | Α | 160 | F | Α | 120 | |
|-------------|-----------------------------------|-------------------------------------------------------------|-----------|-----------|--------|----------|----------|--|
| | | 2 | 3 | 4 | 5 | 6 | 7 | |
| | 1 - Vishay Semiconductors product | | | | | | | |
| | 2 - | 2 - Standard recovery diode | | | | | | |
| | 3 - | - Present silicon generation | | | | | | |
| | 4 - | - Current rating (160 = 160 A) | | | | | | |
| | 5 - | - Circuit configuration (2 separate diodes, parallel pin-ou | | | | | | |
| | 6 - | Pac | kage in | dicator (| SOT-22 | 27 stand | dard ins | |
| | 7 - | Vol | tage rati | ng (120 | = 1200 | V) | | |

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| CIRCUIT CONFI | GURATION | |
|------------------------------------------|-------------------------------|-----------------|
| CIRCUIT DESCRIPTION | CIRCUIT CONFIGURATION CODE | CIRCUIT DRAWING |
| Two separate diodes, parallel pin-out | F | Lead Assignment |

| LINKS TO RELATED DOCUMENTS | | | | | | |
|-------------------------------------|--------------------------|--|--|--|--|--|
| Dimensions www.vishay.com/doc?95423 | | | | | | |
| Packaging information | www.vishay.com/doc?95425 | | | | | |

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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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